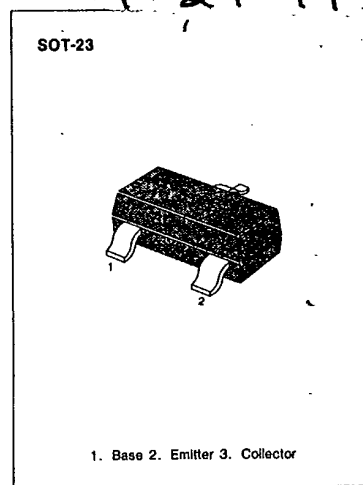


**MMBA811C6****PNP EPTAXIAL SILICON TRANSISTOR****DRIVER TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	50	V
Collector-Emitter Voltage	$V_{CE0}$	45	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Collector Current	$I_C$	50	mA
Collector Dissipation	$P_C$	350	mW
Storage Temperature	$T_{stg}$	150	$^\circ\text{C}$

• Refer to MMBT5086 for graphs

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CB0}$	$I_C=100\mu\text{A}, I_E=0$	50		V
Collector-Emitter Breakdown Voltage	$BV_{CE0}$	$I_C=1.0\text{mA}, I_B=0$	45		V
Emitter-Base Breakdown Voltage	$BV_{EB0}$	$I_E=10\mu\text{A}, I_C=0$	5		V
Collector Cutoff Current	$I_{CB0}$	$V_{CB}=40\text{V}, I_E=0$		50	nA
Emitter Cutoff Current	$I_{EB0}$	$V_{EB}=5.0\text{V}, I_C=0$		50	nA
DC Current Gain	$h_{FE}$	$V_{CE}=3\text{V}, I_C=0.1\text{mA}$	150		
		$V_{CE}=3\text{V}, I_C=0.5\text{mA}$	200	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$		0.3	V
Current Gain-Bandwidth Product	$f_t$	$I_C=1.0\text{mA}, V_{CE}=6.0\text{V}$ $f=100\text{MHz}$	75		MHz

**Marking**